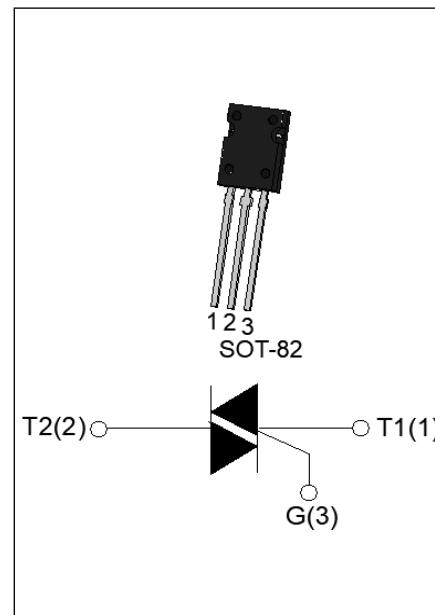


**DESCRIPTION:**

The JST134QP-600T triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package SOT-82 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(\text{RMS})}$	4	A
$V_{\text{DRM}} / V_{\text{RRM}}$	600	V
$I_{\text{GT I/II/III/IV}}$	5/5/5/5	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{\text{stg}}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{DRM}}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{RRM}}$	600	V
RMS on-state current ( $T_c \leqslant 84^\circ\text{C}$ )	$I_{T(\text{RMS})}$	4	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{\text{TSM}}$	25	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		27.5	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	3.125	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{\text{GT}}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	I - II III-IV	30 20	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{\text{GM}}$	2	
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{\text{G(AV)}}$	0.5	W
Peak gate power	$P_{\text{GM}}$	5	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive,off-state;FIG.7)	$V_{\text{pp}}$	2.5	kV

ELECTRICAL CHARACTERISTICS ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	ALL	MAX.	5	mA
$V_{GT}$		ALL	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III-IV	MAX.	9	mA
		II		13	
$I_H$	$I_T=100\text{mA}$		MAX.	5	mA
$dV/dt$	$V_D=400\text{V}$ Gate Open $T_j=110^\circ\text{C}$		MIN.	30	V/ $\mu\text{s}$
$(dV/dt)_c$	$(dl/dt)c=1.8\text{A/ms}$ , $T_j=110^\circ\text{C}$		MIN.	1.2	V/ $\mu\text{s}$
$t_{on}$	$I_G=10\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	2	$\mu\text{s}$	
			20		

## STATIC CHARACTERISTICS

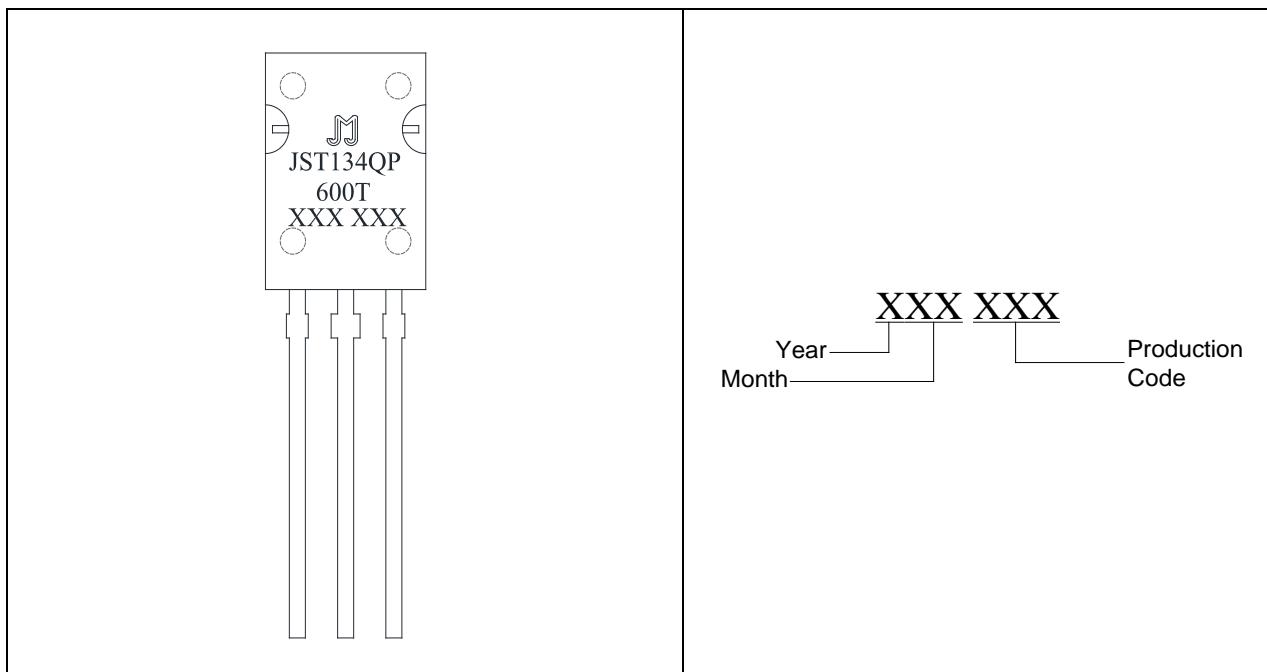
Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=5\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55
$V_{TO}$	Threshold voltage		$T_j=125^\circ\text{C}$	0.92
$R_D$	Dynamic resistance		$T_j=125^\circ\text{C}$	107
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	0.25	mA

## THERMAL RESISTANCES

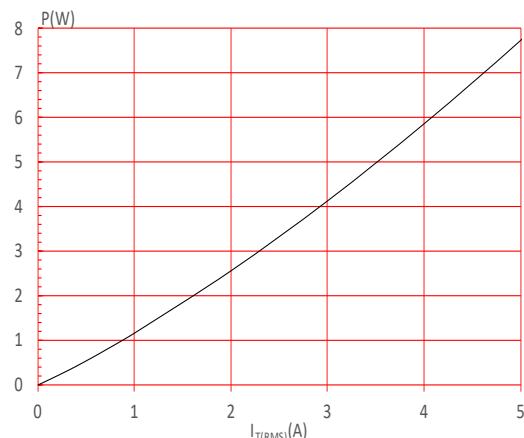
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	7.0	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	150	$^\circ\text{C}/\text{W}$

**ORDERING INFORMATION**

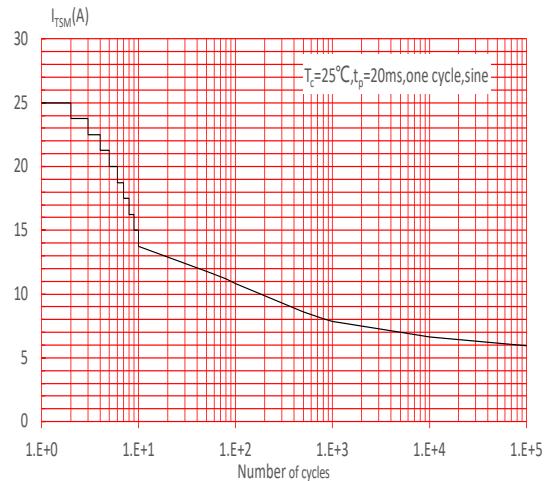
<b>J</b>	<b>ST</b>	<b>134</b>	<b>QP</b>	<b>-600</b>	<b>T</b>
JieJie Microelectronics Co., Ltd.					
	Triacs				
		<u><math>I_T(\text{RMS}):4A</math></u>			
			<u>QP:SOT-82</u>		
				<u><math>600:V_{DRM} / V_{RRM} \geq 600V</math></u>	
					<u><math>T: I_{GT1-4} \leq 5mA</math></u>

**MARKING**

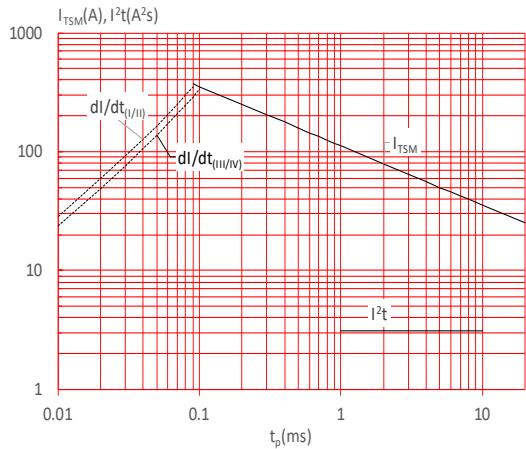
**FIG.1** Maximum power dissipation versus RMS on-state current



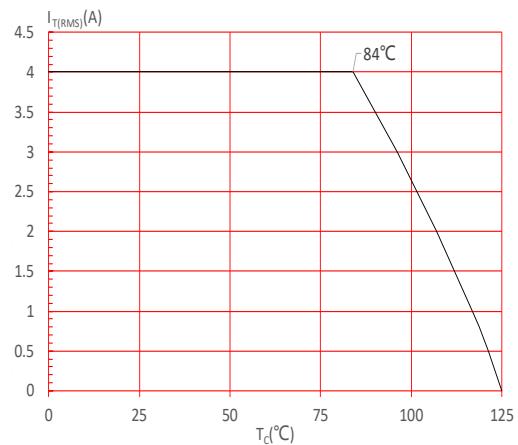
**FIG.3:** Surge peak on-state current versus number of cycles



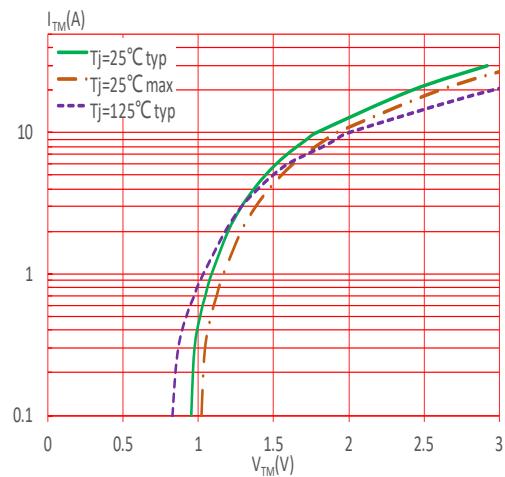
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( I - II :  $dl/dt < 30\text{A}/\mu\text{s}$ ; III - IV :  $dl/dt < 20\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

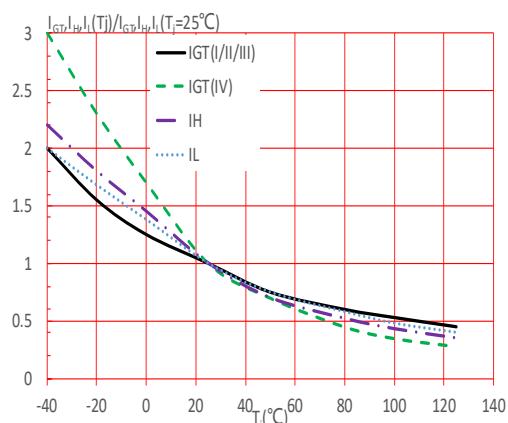
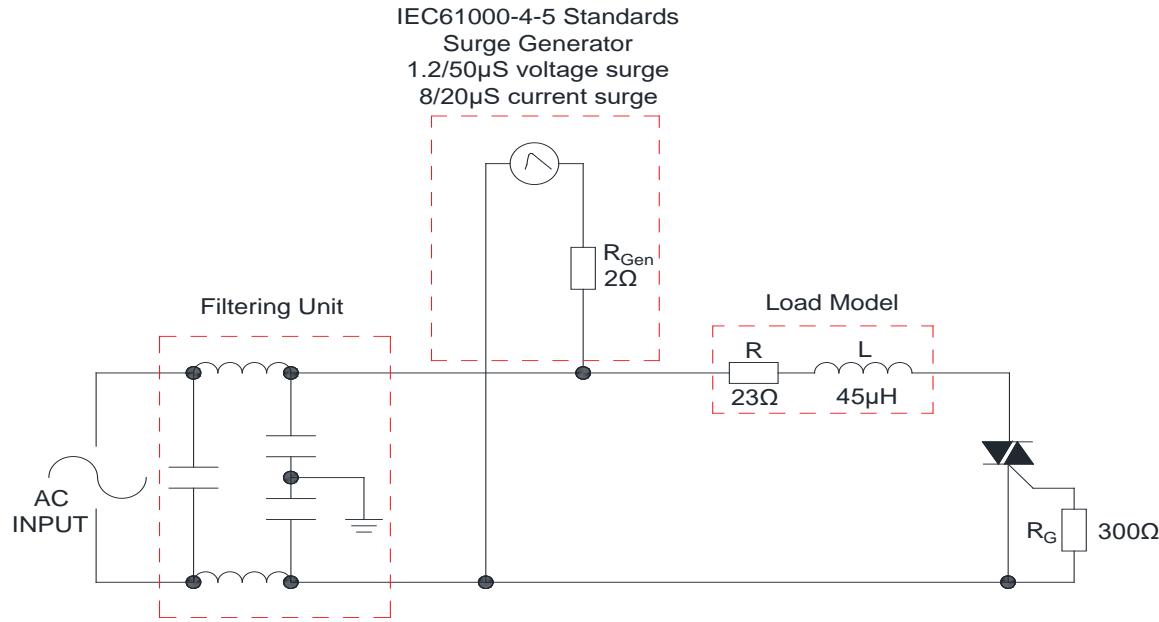


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

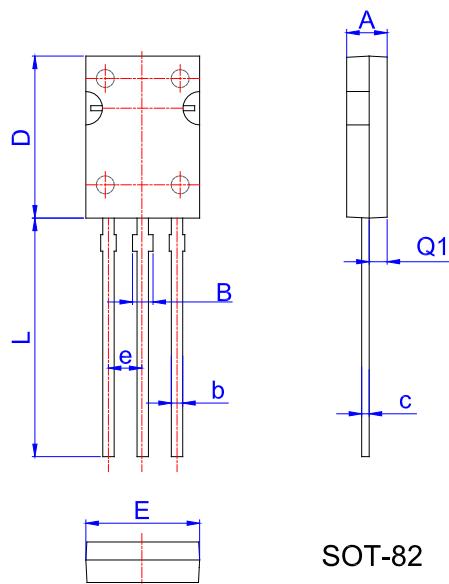
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III-IV			
<b>JST134QP-600T</b>	600	5	SOT-82	500	<b>Bulk Pack</b>

**Document Revision History**

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.45	2.55	2.65	0.096	0.100	0.104
b	0.71	0.76	0.81	0.028	0.030	0.032
B	1.27	1.37	1.45	0.050	0.054	0.057
c	0.48	0.50	0.52	0.019	0.020	0.021
D	10.60	10.80	11.00	0.417	0.425	0.433
E	7.30		7.70	0.287		0.303
e	2.24	2.29	2.34	0.088	0.090	0.092
L	15.30	15.60	15.90	0.602	0.614	0.626
Q1	1.17	1.27	1.37	0.046	0.050	0.054

## DELIVERY MODE

PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	CARTON BOX (PCS)
SOT-82	Bulk Pack	500	2,000	10,000

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